

# **ZX5T951GTA Datasheet**



https://www.DiGi-Electronics.com

DiGi Electronics Part Number ZX5T951GTA-DG

Manufacturer Diodes Incorporated

Manufacturer Product Number ZX5T951GTA

Description TRANS PNP 60V 5.5A SOT223-3

Detailed Description Bipolar (BJT) Transistor PNP 60 V 5.5 A 120MHz 3 W

Surface Mount SOT-223-3



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
ZX5T951GTA	Diodes Incorporated
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	5.5 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
60 V	250mV @ 500mA, 5A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
20nA (ICBO)	100 @ 2A, 1V
Power - Max:	Frequency - Transition:
3 W	120MHz
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
TO-261-4, TO-261AA	SOT-223-3
Base Product Number:	
ZX5T951	

# **Environmental & Export classification**

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0075	





#### **60V PNP MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT223**

#### **Features**

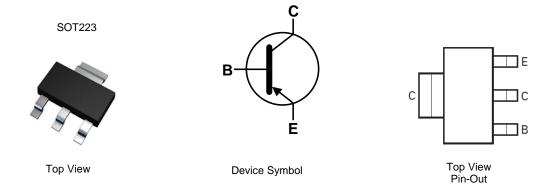
- BV<sub>CEO</sub> > -60V
- I<sub>C</sub> = -5.5A High Continuous Collector Current
- I<sub>CM</sub> = -15A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < -70mV @ -1A</li>
- R<sub>SAT</sub> = 39mΩ for a Low Equivalent On-Resistance
- h<sub>FE</sub> Specified Up to -10A for a High Gain Hold Up
- Complementary NPN Type: ZX5T851G
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
   Solderable per MIL-STD-202, Method 208 (2)
- Weight: 0.112 grams (Approximate)

#### **Applications**

- DC-DC Converters
- MOSFET & IGBT Gate Drivers
- Charging Circuits
- Power Switches
- Motor Control



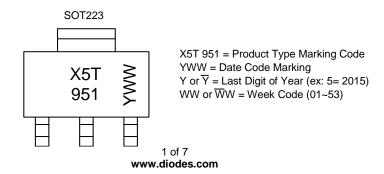
#### Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZX5T951GTA	X5T951	7	12	1,000
ZX5T951GTC	X5T951	13	12	4,000

Notes

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

#### **Marking Information**



ZX5T951G Datasheet Number: DS33424 Rev. 4 - 2



### 

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-100	V
Collector-Emitter Voltage	$V_{\sf CEO}$	-60	V
Emitter-Base Voltage	$V_{EBO}$	-7	V
Continuous Collector Current	Ic	-5.5	Α
Peak Pulse Current	I <sub>CM</sub>	-15	Α

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)	0	3.0 24	W	
Linear Derating Factor	(Note 6)	P <sub>D</sub>	1.6 12.8	mW /°C	
Thermal Decistores, Junction to Ambient	(Note 5)	$R_{\theta JA}$	42		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	78	°C/W	
Thermal Resistance Junction to Lead	(Note 7)	$R_{ heta JL}$	10.48		
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

### ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

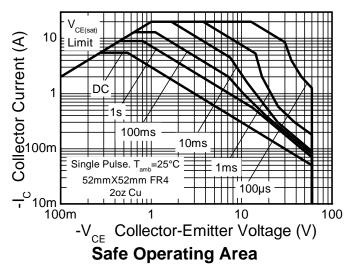
- 5. For a device surface mounted on 52mm x 52mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Same as Note (5), except the device is surface mounted on 25mm x 25mm with 1oz copper.

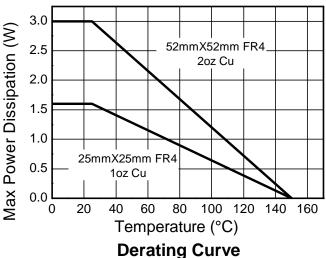
  7. Thermal resistance from junction to solder-point (at the end of the collector lead).

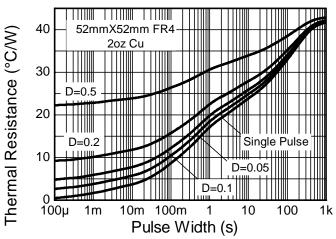
  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

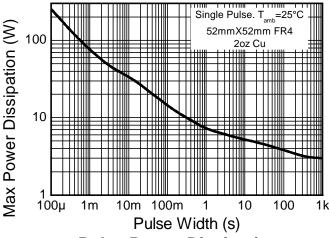


#### **Thermal Characteristics and Derating Information**





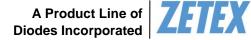




**Transient Thermal Impedance** 

**Pulse Power Dissipation** 







ZX5T951G

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

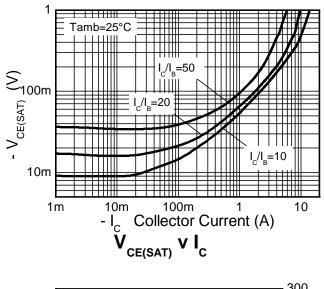
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-100	-120	-	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage	BV <sub>CER</sub>	-100	-120	-	V	$I_C = -1\mu A$ , RB $\leq 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-60	-80	-	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	-8.1	-	V	$I_E = -100 \mu A$
Collector-Base Cutoff Current	I <sub>CBO</sub>	-	<1 -	-20 -0.5	nΑ μΑ	V <sub>CB</sub> = -80V V <sub>CB</sub> = -80V, T <sub>A</sub> = +100°C
Collector-Emitter Cutoff Current	l <sub>CER</sub> R≤1kΩ	-	<1 -	-20 -0.5	nΑ μΑ	V <sub>CB</sub> = -80V V <sub>CB</sub> = -80V, T <sub>A</sub> = +100°C
Emitter Cutoff Current	I <sub>EBO</sub>	-	<1	-10	nA	V <sub>EB</sub> = -6V
	hFE	100	250	-		$I_C = -10 \text{mA}, V_{CE} = -1 \text{V}$
Static Forward Current Transfer Datic (Note 0)		100	200	300		$I_C = -2A$ , $V_{CE} = -1V$
Static Forward Current Transfer Ratio (Note 9)		45	90	-	-	I <sub>C</sub> = -5A, V <sub>CE</sub> = -1V
		10	25	-		$I_C = -10A$ , $V_{CE} = -1V$
	V <sub>CE(sat)</sub>	-	-15	-25		$I_C = -100 \text{mA}, I_B = -10 \text{mA}$
Collector Emitter Seturation Voltage (Note 0)		-	-55	-70	mV	$I_C = -1A$ , $I_B = -100mA$
Collector-Emitter Saturation Voltage (Note 9)		-	-90	-120	IIIV	$I_C = -2A$ , $I_B = -200mA$
		-	-195	-250		$I_C = -5A$ , $I_B = -500mA$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(sat)}$	-	-1,030	-1,150	mV	$I_C = -5A$ , $I_B = -500$ mV
Base-Emitter Turn-On Voltage (Note 9)	V <sub>BE(on)</sub>	-	-920	-1,020	mV	$I_C = -5A$ , $V_{CE} = -1V$
Output Capacitance (Note 9)	$C_{obo}$	-	48	-	pF	V <sub>CB</sub> = -10V. f = 1MHz
Transition Frequency	f <sub>T</sub>	-	120	-	MHz	V <sub>CE</sub> = -10V, I <sub>C</sub> = -100mA f = 50MHz
Switching Time	t <sub>on</sub>	-	39	-	ns	$V_{CC} = -10V, I_{C} = -1A$
Switching Time	t <sub>off</sub>	-	370	-	115	$I_{B1} = -I_{B2} = -100 \text{mA}$

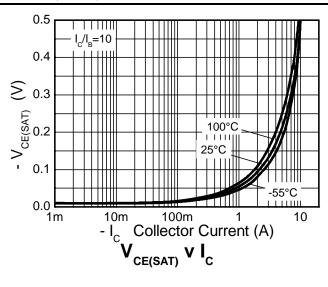
Note:

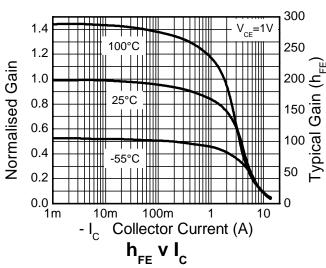
9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.

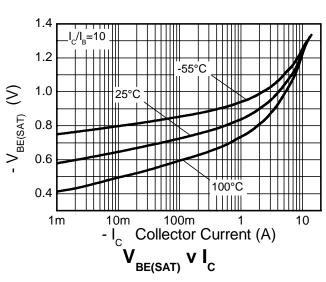


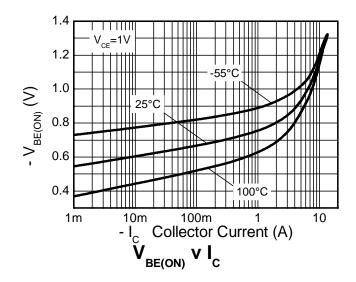
### Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)







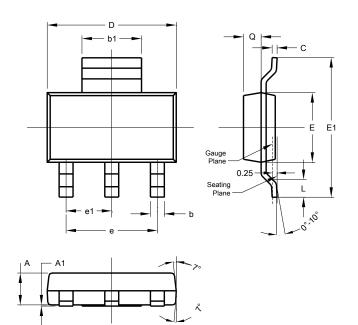






### **Package Outline Dimensions**

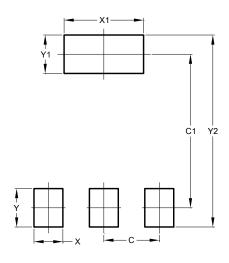
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_	_	4.60		
e1	_	_	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



#### **IMPORTANT NOTICE**

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

#### LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2015, Diodes Incorporated

www.diodes.com



### **OUR CERTIFICATE**

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we striciy control the quality of products and services. Welcome your RFQ to Email: Info@DiGi-Electronics.com

















Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com